AMENDMENTS TO THE CLAIMS

Please add or amend the claims to read as follows, and cancel without prejudice or disclaimer to resubmission in a divisional or continuation application claims indicated as cancelled:

1. (Currently amended) A method of reading data in a virtual ground array of memory cells comprising: sensing substantially simultaneously a state of adjacent memory cells through at least a partially shared sensing path including a common sense amplifier, wherein sensing includes applying a first voltage to a common word line and a substantially similar voltage to source side bitlines of the cells ~~either a shared bit line or to non-shared bit lines~~.

2. (Original) The method of claim 1, wherein said sensing substantially simultaneously comprises: coupling a sense amplifier to a first source/drain terminal of each cell of said adjacent memory cells; setting a voltage at a second drain/source terminal of each cell of said adjacent cells to a read level; and sensing in a reading direction the state of said adjacent cells.

3. (Original) The method according to claim 1, wherein said adjacent cells share at least a word line.

4. (Original) The method according to claim 1, wherein said adjacent cells share at least an inside bit line.

5. (Currently amended) The method according to claim [[1]] 2, wherein said coupling a sense amplifier to a first source/drain further comprising coupling said sense amplifier to a shared bit line of said adjacent cells.

6. (Currently amended) The method according to claim [[1]] 2, wherein said coupling a sense amplifier to a first source/drain further comprising coupling said sense amplifier to bit lines of said adjacent cells that are not shared by said adjacent cells.

7. (Original) The method according to claim 1, wherein any one of said memory cells stores at least one bit in said charge trapping region.

8. (Original) The method according to claim 1, wherein said adjacent cells are sensed with substantially identical current.

9. (Original) The method according to claim 1, wherein said memory cells are nitride read only memory (NROM) cells.

10. (Currently amended) The method according to claim [[1]] 2, wherein said coupling a sense amplifier to a first source/drain further comprising coupling said sense amplifier through select transistors to said shared or not shared bit lines.

11. (Currently amended) The method according to claim [[1]] 2, wherein said coupling a sense amplifier to a first source/drain further comprising coupling said sense amplifier substantially directly to said not shared bit lines.

12. – 17. (Withdrawn)